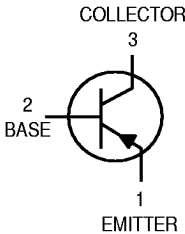


Amplifier Transistors

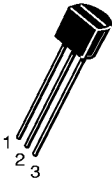
PNP Silicon

Boca Semiconductor Corp. (BSC)



2N5400
2N5401*

*Motorola Preferred Device



CASE 29-04, STYLE 1
TO-92 (TO-226AA)

MAXIMUM RATINGS

Rating	Symbol	2N5400	2N5401	Unit
Collector–Emitter Voltage	V_{CEO}	120	150	Vdc
Collector–Base Voltage	V_{CBO}	130	160	Vdc
Emitter–Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0		mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12		Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ⁽¹⁾ ($I_C = 1.0 \text{ mAdc}$, $I_B = 0$)	2N5400 2N5401	$V_{(BR)CEO}$	120 150	— —	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}$, $I_E = 0$)	2N5400 2N5401	$V_{(BR)CBO}$	130 160	— —	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}$, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 100 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = 120 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = 100 \text{ Vdc}$, $I_E = 0$, $T_A = 100^\circ\text{C}$) ($V_{CB} = 120 \text{ Vdc}$, $I_E = 0$, $T_A = 100^\circ\text{C}$)	2N5400 2N5401 2N5400 2N5401	I_{CBO}	— — — —	100 50 100 50	nAdc μAdc
Emitter Cutoff Current ($V_{EB} = 3.0 \text{ Vdc}$, $I_C = 0$)		I_{EBO}	—	50	nAdc

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2.0%.

2N5400 2N5401**ELECTRICAL CHARACTERISTICS** ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS(1)				
DC Current Gain ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	30	—	—
2N5400		50	—	—
2N5401		40	180	—
($I_C = 10\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$)		60	240	—
($I_C = 50\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	40	—	—
2N5400		50	—	—
2N5401		—	—	—
Collector–Emitter Saturation Voltage ($I_C = 10\text{ mAdc}$, $I_B = 1.0\text{ mAdc}$)	$V_{CE(sat)}$	—	0.2	Vdc
($I_C = 50\text{ mAdc}$, $I_B = 5.0\text{ mAdc}$)		—	0.5	Vdc
Base–Emitter Saturation Voltage ($I_C = 10\text{ mAdc}$, $I_B = 1.0\text{ mAdc}$)	$V_{BE(sat)}$	—	1.0	Vdc
($I_C = 50\text{ mAdc}$, $I_B = 5.0\text{ mAdc}$)		—	1.0	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	400	MHz
2N5400		100	300	MHz
2N5401		—	—	—
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	—	6.0	pF
Small–Signal Current Gain ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	30	200	—
2N5400		40	200	—
2N5401		—	—	—
Noise Figure ($I_C = 250\text{ }\mu\text{Adc}$, $V_{CE} = 5.0\text{ Vdc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$)	NF	—	8.0	dB

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2.0%.

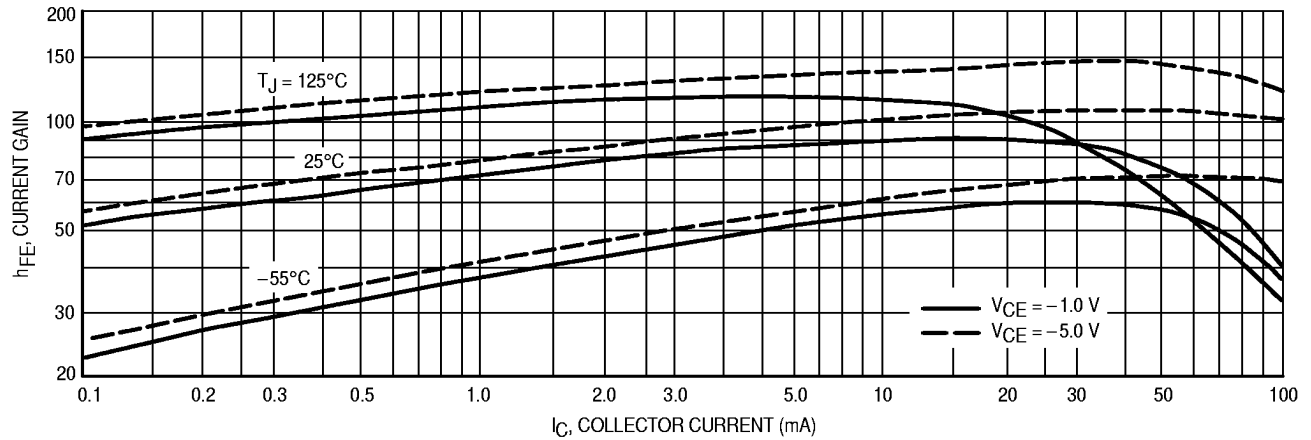


Figure 1. DC Current Gain

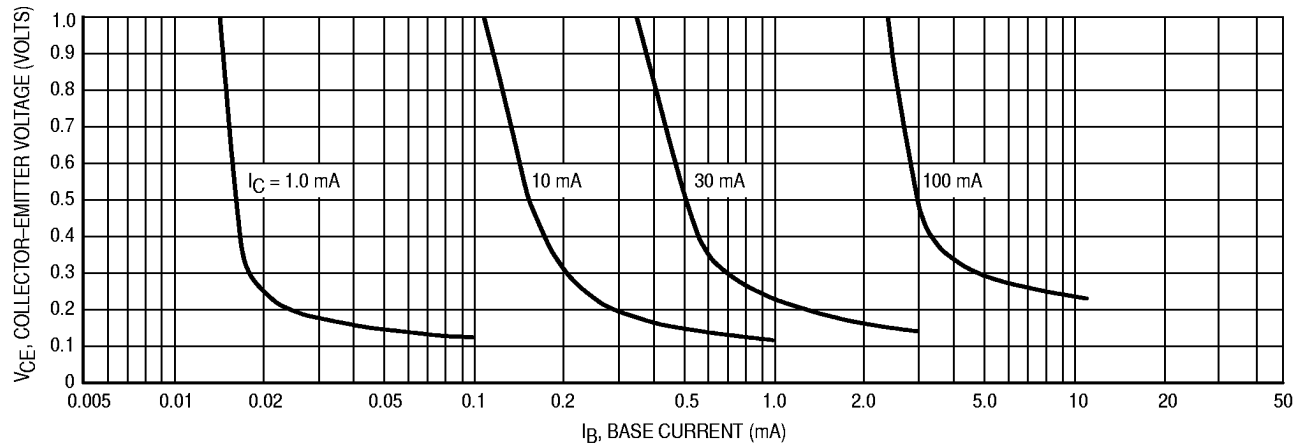


Figure 2. Collector Saturation Region

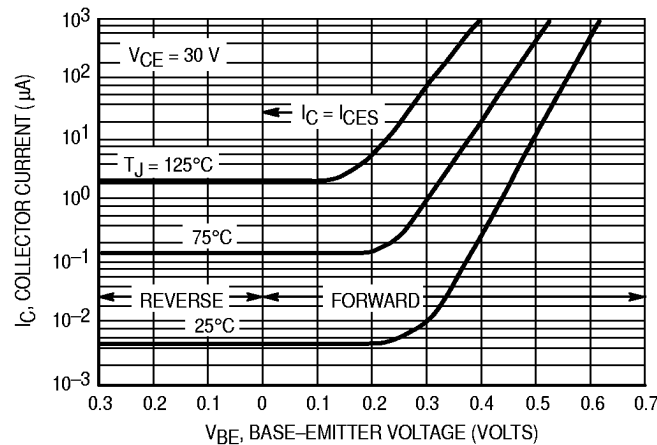


Figure 3. Collector Cut-Off Region

2N5400 2N5401

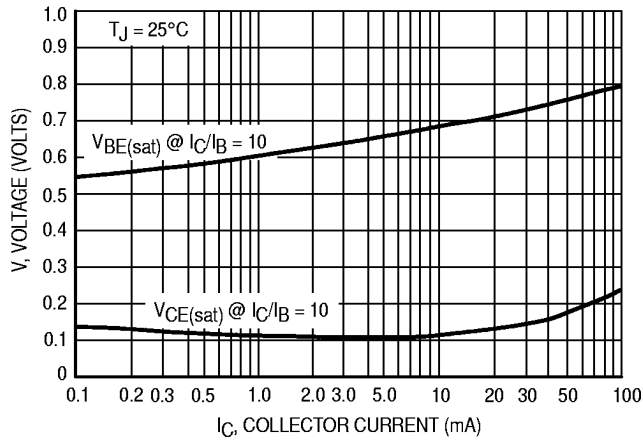


Figure 4. "On" Voltages

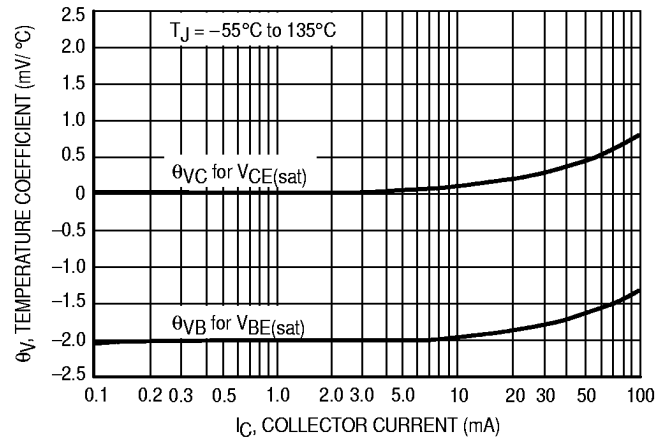
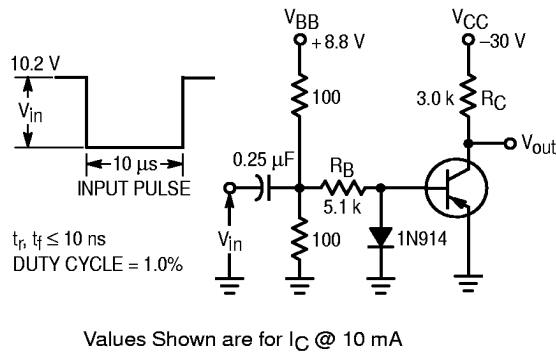


Figure 5. Temperature Coefficients



Values Shown are for I_C @ 10 mA

Figure 6. Switching Time Test Circuit

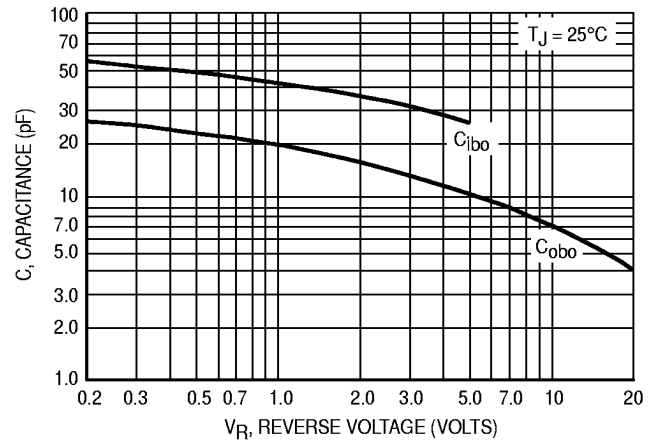


Figure 7. Capacitances

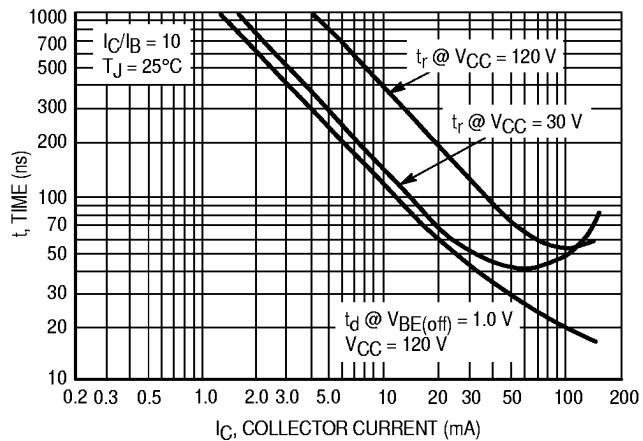


Figure 8. Turn-On Time

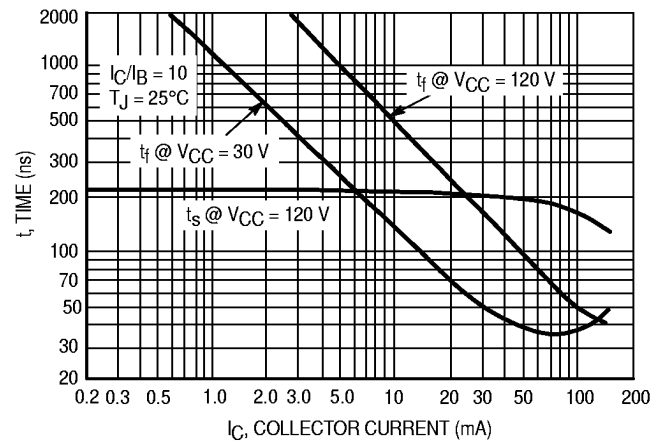
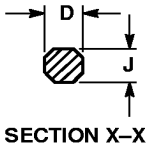
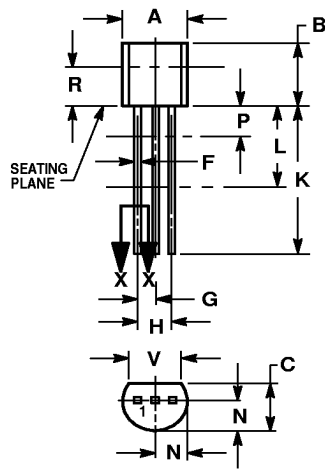


Figure 9. Turn-Off Time

PACKAGE DIMENSIONS



CASE 029-04
(TO-226AA)
ISSUE AD

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K. MINIMUM LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

- STYLE 1:
1. PIN 1. EMITTER
 2. BASE
 3. COLLECTOR